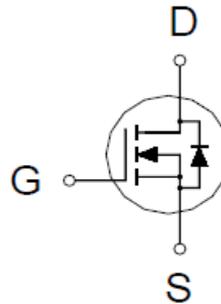
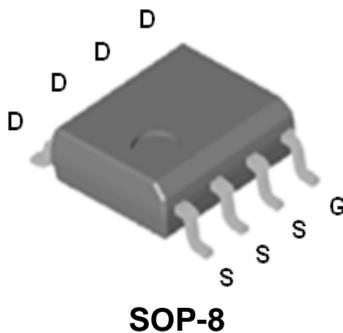


P2202CV

N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
20V	22m Ω @ $V_{GS} = 4.5V$	8A



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ²	I_D	$T_A = 25\text{ }^\circ\text{C}$	8
		$T_A = 70\text{ }^\circ\text{C}$	6
Pulsed Drain Current ^{1,2}	I_{DM}	80	A
Avalanche Current	I_{AS}	20	
Avalanche Energy	E_{AS}	21	mJ
Power Dissipation	P_D	$T_A = 25\text{ }^\circ\text{C}$	2.5
		$T_A = 70\text{ }^\circ\text{C}$	1.6
Operating Junction & Storage Temperature Range	T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ³	$R_{\theta JA}$		50	$^\circ\text{C} / \text{W}$

¹Pulse width limited by maximum junction temperature.

²Limited only by maximum temperature allowed.

³The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

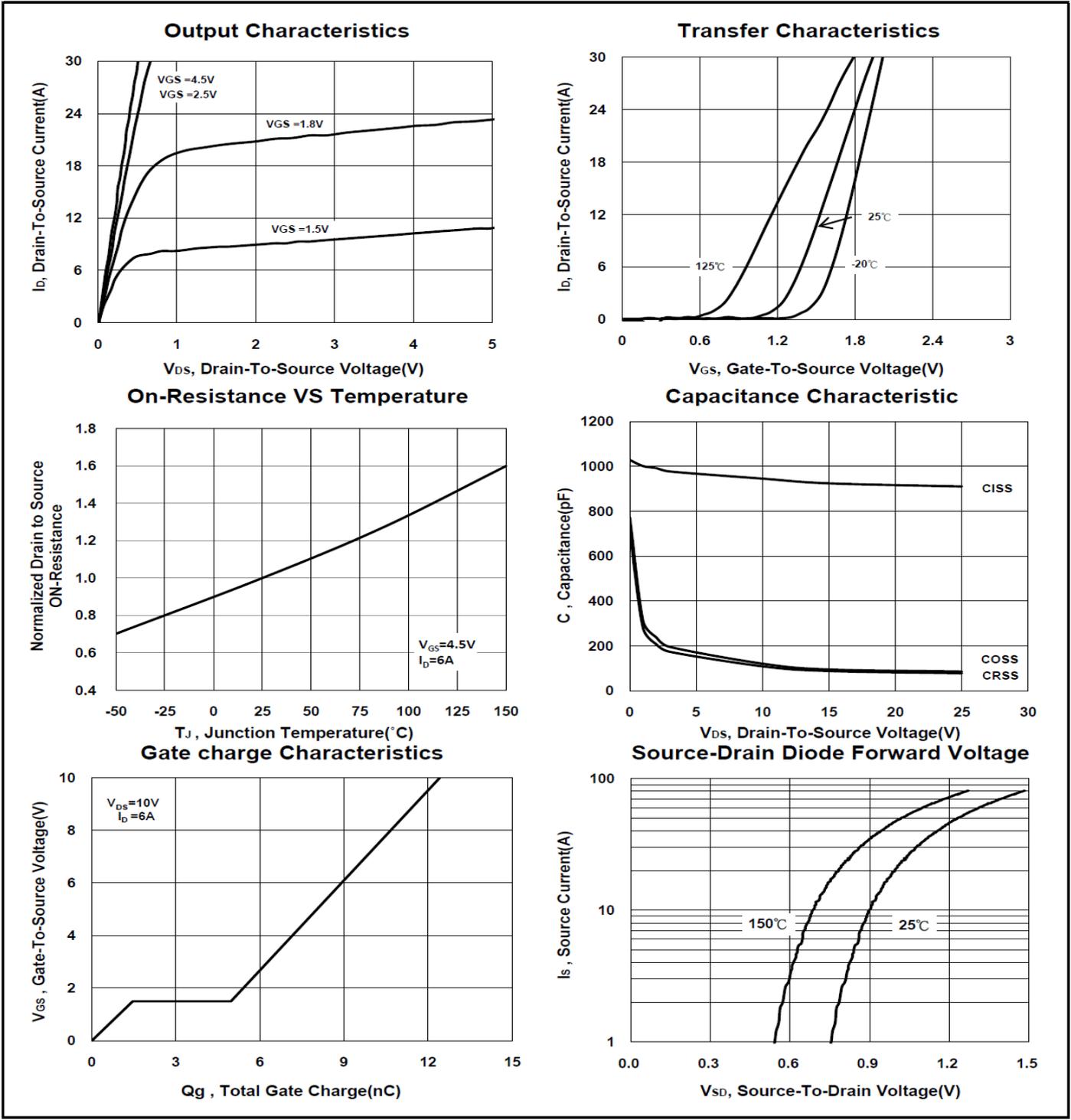
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.5	0.7	1	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±8V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16V, V _{GS} = 0V			1	μA
		V _{DS} = 10V, V _{GS} = 0V, T _J = 70 °C			10	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 5V	80			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 6A		15	22	mΩ
		V _{GS} = 2.5V, I _D = 5A		19	26	
		V _{GS} = 1.8V, I _D = 4A		26	34	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 6A		33		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz		967		pF
Output Capacitance	C _{oss}			124		
Reverse Transfer Capacitance	C _{rss}			115		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		3.1		
Total Gate Charge ²	Q _g	V _{DS} = 0.5V _{(BR)DSS} , V _{GS} = 4.5V, I _D = 6A		12.7		nC
Gate-Source Charge ²	Q _{gs}			1.6		
Gate-Drain Charge ²	Q _{gd}			4.1		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 0.5V _{(BR)DSS} , I _D ≅ 6A, V _{GS} = 4.5V, R _{GEN} = 6Ω		30		nS
Rise Time ²	t _r			120		
Turn-Off Delay Time ²	t _{d(off)}			70		
Fall Time ²	t _f			70		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Continuous Current	I _S				8	A
Forward Voltage ¹	V _{SD}	I _F = 6A, V _{GS} = 0V			1	V
Reverse Recovery Time	t _{rr}	I _F = 6A, di _F /dt = 100A /μS		13		nS
Reverse Recovery Charge	Q _{rr}				4	

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

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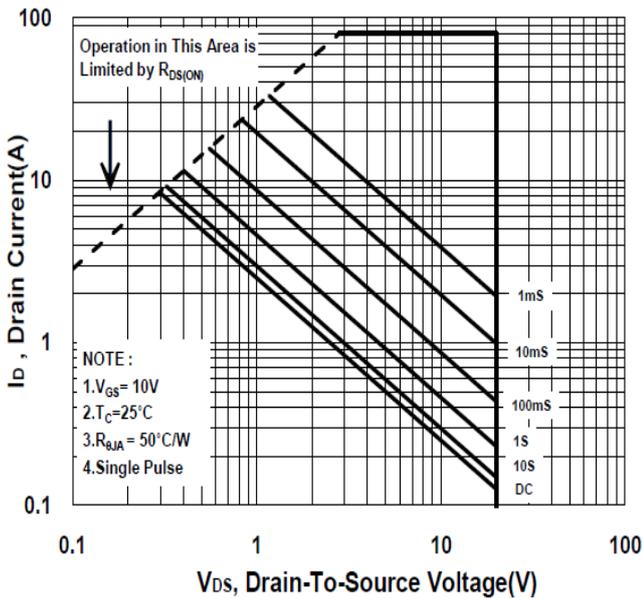
N-Channel Enhancement Mode MOSFET



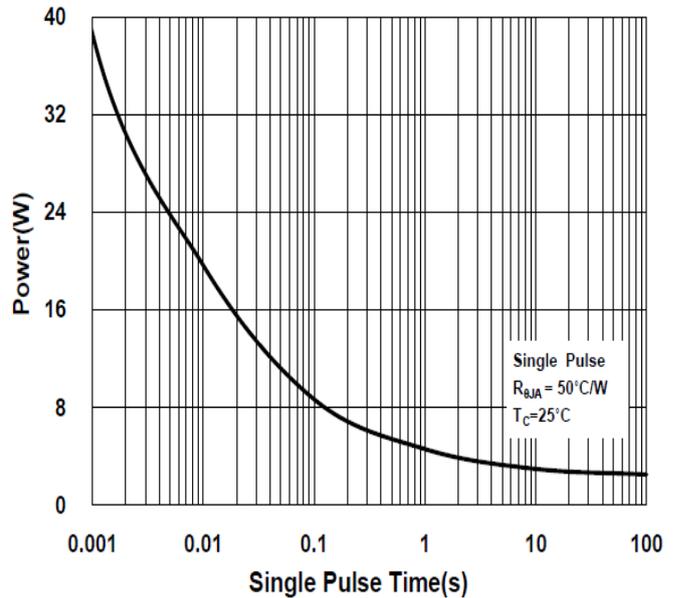
P2202CV

N-Channel Enhancement Mode MOSFET

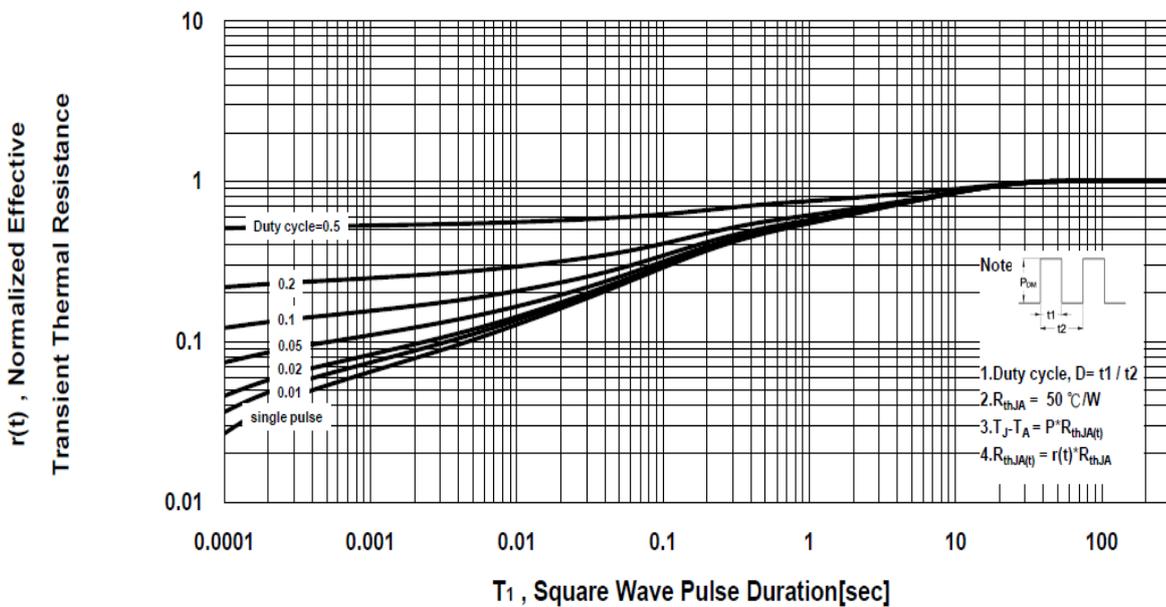
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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Package Dimension

SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25				

